

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UFT30-28S** is Designed for

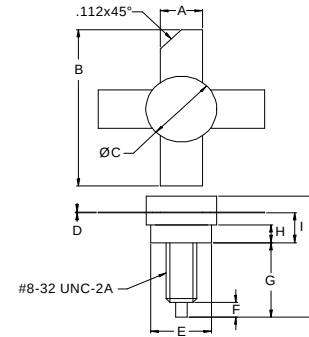
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .380 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10666

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CEO}	I _C = 50 mA		35			V
BV _{CER}	I _C = 50 mA	R _{BE} = 10 Ω	60			V
BV _{EBO}	I _E = 10 mA		4.0			V
I _{CES}	V _E = 28 V				5	mA
h _{FE}	V _{CE} = 5.0 V	I _C = 1.0 A	10		100	---
C _{ob}	V _{CB} = 28 V		f = 1.0 MHz		80	pF
P _{GE}	V _{CE} = 25 V	I _{CQ} = 3.2 A	f = 225 MHz	13.5	14.5	dB
IMD ₃	P _{REF} = 16 W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB		-55	dBc